

Description

A proprietary structure is used in achieving ultra-low $V_{CE(sat)}$ performance and reduced operating temperature. This has the benefit of reducing thermal management requirements and increasing long-term reliability.

Features

- $BV_{CEO} > 60V$
- 5.5A Continuous Collector Current
- Low Saturation Voltage $V_{CE(sat)} < 45mV @ 1A$
- High Current $R_{CE(sat)} typ = 24m\Omega$
- h_{FE} Characterized up to 6A
- 2W Power Dissipation
- Fast Switching with Short Storage Time
- Sidewall Tin Plating for Wettable Flanks in AOI
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact_us@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

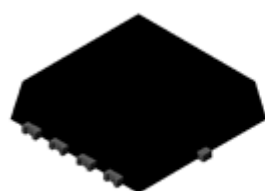
Applications

- Medium-power DC-DC converters
- High-side/low-side switches
- Linear voltage regulation

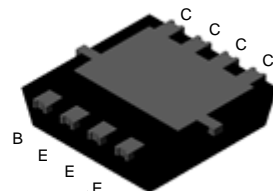
Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic. "Green" Molding Compound
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Solderable per MIL-STD-202, Method 208 (G3)
- Weight: 0.03 grams (Approximate)

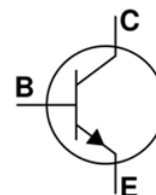
PowerDI3333-8/SWP (Type UX)



Top View



Bottom View



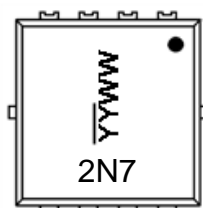
Device Symbol

Ordering Information (Note 4)

Orderable Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
					Qty.	Carrier
DXTN69060CFG-7	PowerDI3333-8/SWP (Type UX)	2N7	7	12	2,000	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



2N7 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 25 = 2025)
WW = Week Code (01 to 53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current (Note 5)	I _C	5.5	A
Continuous Collector Current (Note 6)	I _C	3.5	A
Peak Pulse Current	I _{CM}	12	A
Base Current	I _B	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	2	W mW/°C
		16	
		1.35	
		10.8	
Thermal Resistance, Junction to Ambient	R _{θJA}	0.9	°C/W
		7.2	
		62.5	
		92	
Thermal Resistance, Junction to Lead	R _{θJL}	139	°C/W
		8.5	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

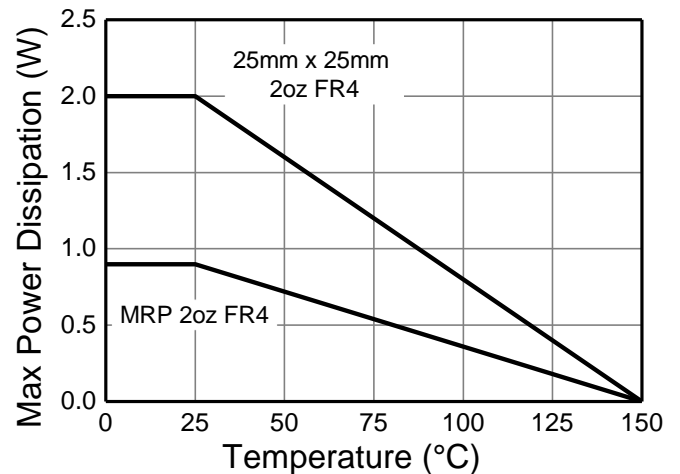
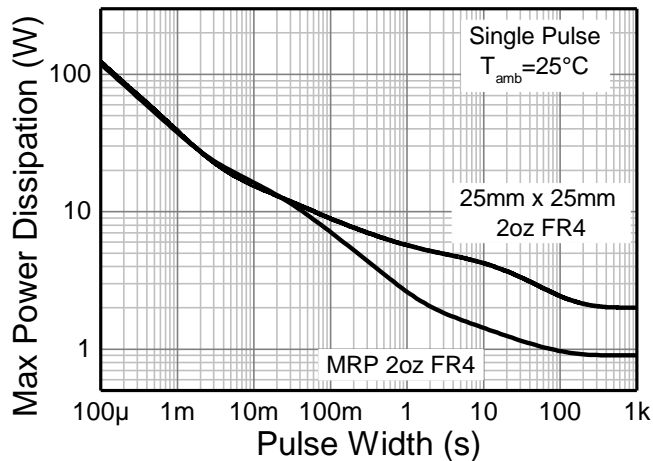
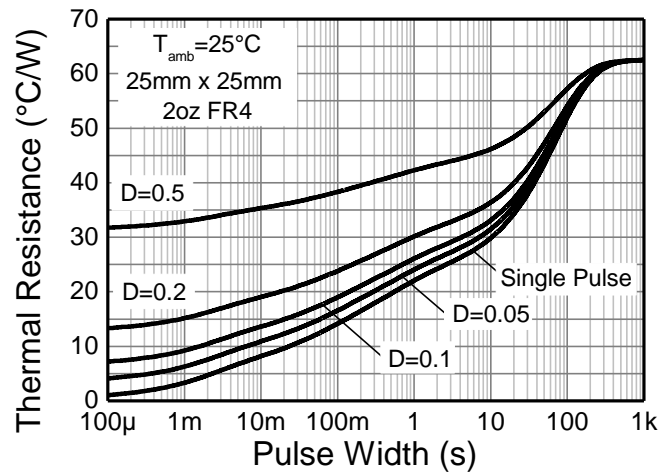
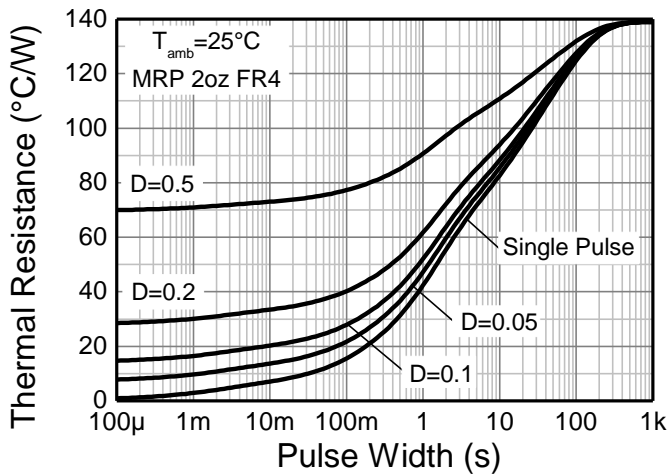
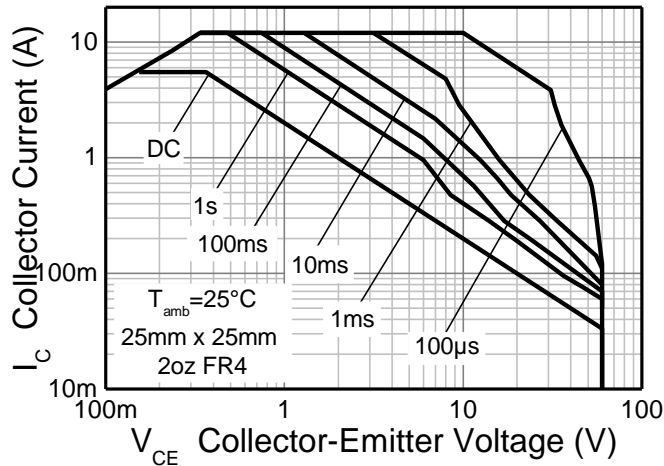
- For a device mounted with the exposed collector pad on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.
- Same as Note 5, except the device is mounted on 15mm x 15mm 2oz copper.
- Same as Note 5, except the device is mounted on minimum recommended pad layout.
- Thermal resistance from junction to solder-point (at the end of the collector lead).

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C
Electrostatic Discharge – Charged Device Model	ESD CDM	1,000	V	IV

Note: 9. Refer to JEDEC specification JESD22-A114, JESD22-A115 and JESD22-C101.

Thermal Characteristics and Derating Information



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Base Open) (Note 10)	BV _{CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	100 0.5	nA μA	V _{CB} = 80V V _{CB} = 80V, T _A = +100°C
Emitter-Base Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 6V
ON CHARACTERISTICS (Note 10)						
Static Forward Current Transfer Ratio	h _{FE}	250 200 80	360 325 170	475 — —	—	I _C = 100mA, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	30 70 70 135 170	45 95 100 170 220	mV	I _C = 1A, I _B = 100mA I _C = 1A, I _B = 10mA I _C = 2A, I _B = 40mA I _C = 5.5A, I _B = 550mA I _C = 5.5A, I _B = 150mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	1,050 890	1,150 —	mV	I _C = 5.5A, I _B = 550mA I _C = 5.5A, I _B = 150mA
Base-Emitter On Voltage	V _{BE(on)}	—	760	900	mV	I _C = 5.5A, V _{CE} = 2V
SWITCHING CHARACTERISTICS						
Transition Frequency	f _T	—	200	—	MHz	I _C = 100mA, V _{CE} = 10V f = 100MHz
Input Capacitance	C _{ibo}	—	380	—	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	—	23	—	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _d	—	81	—	ns	V _{CC} = 24V, I _C = 750mA I _{B1} = -I _{B2} = 15mA See Fig 6.
Rise Time	t _r	—	64	—	ns	
Storage Time	t _s	—	640	—	ns	
Fall Time	t _f	—	78	—	ns	
Delay Time	t _d	—	87	—	ns	V _{CC} = 48V, I _C = 750mA I _{B1} = -I _{B2} = 15mA See Fig 6.
Rise Time	t _r	—	117	—	ns	
Storage Time	t _s	—	510	—	ns	
Fall Time	t _f	—	101	—	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Timing Waveform

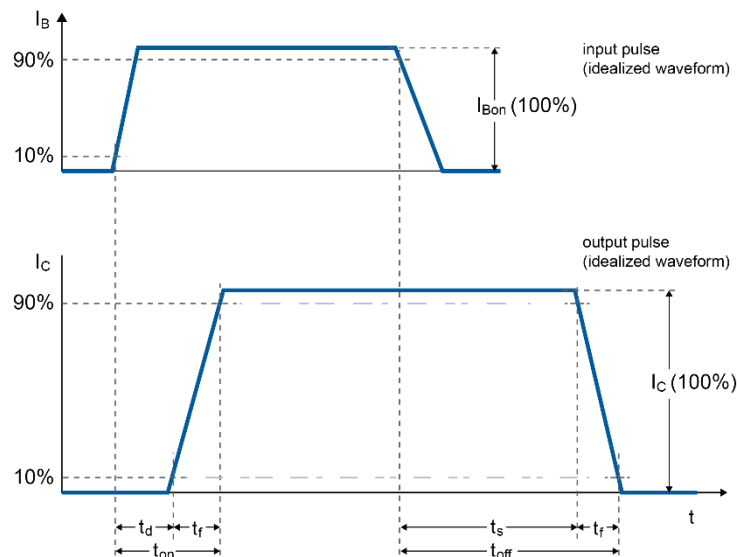
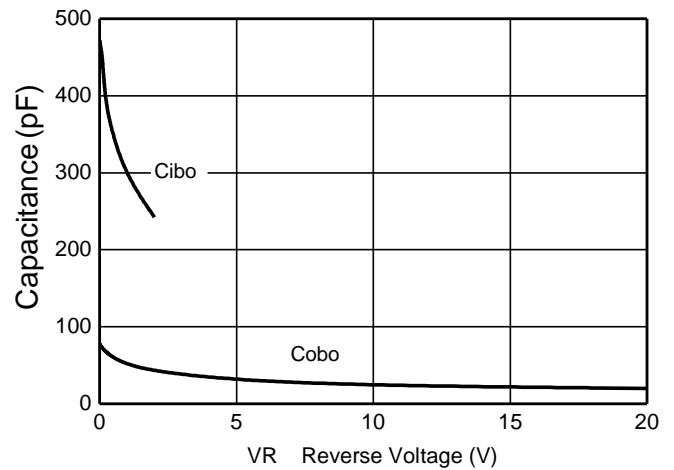
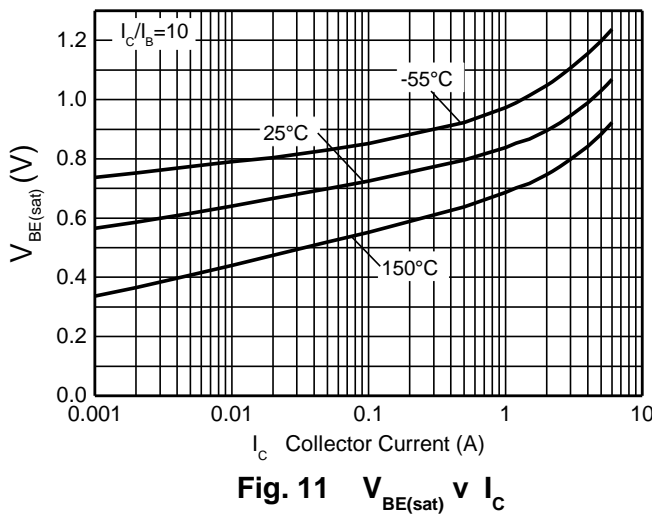
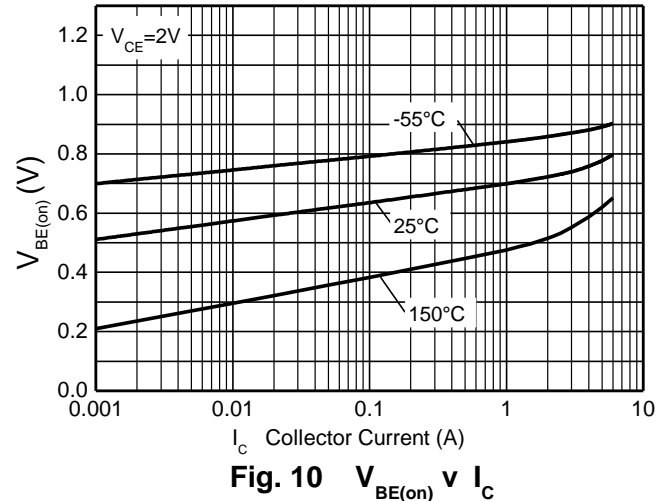
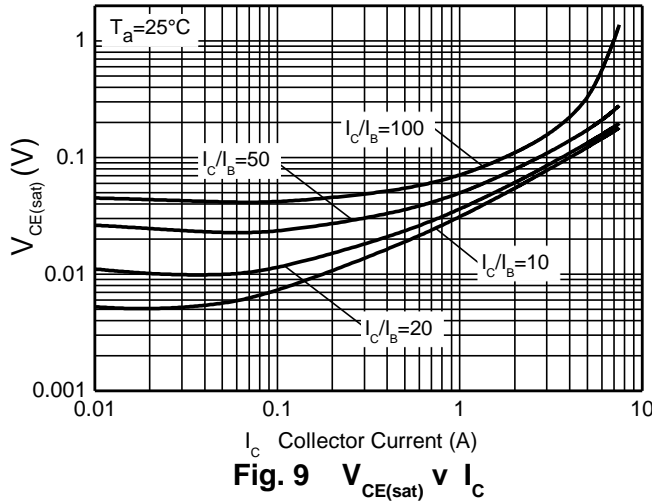
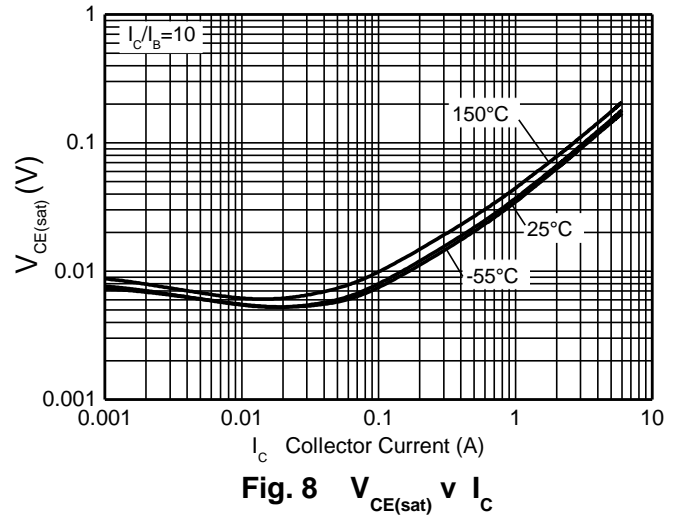
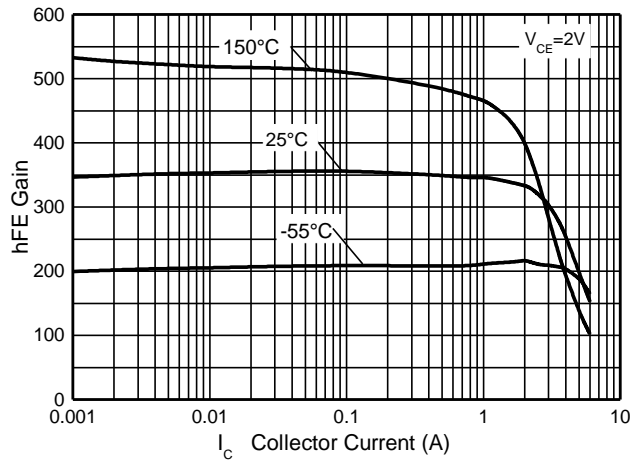


Fig 6. Timing Waveform

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Application Notes

Fig. 13 shows the DXTN69060CFG as a low-side switch. When driving high-current inductive loads, it is recommended to apply appropriate protective measures to manage the kick-back voltage that builds up due to the collapse of the inductor's magnetic field after a switch-off event. The voltage spikes that originate this way can potentially overstress the device above its Maximum Ratings. During evaluation, ensure that the Collector-Emitter Voltage stays below V_{CE0} rating of 60V. An easy way to suppress induced voltage spikes is to place an additional free-wheeling diode in parallel with the load as shown in Fig. 14.

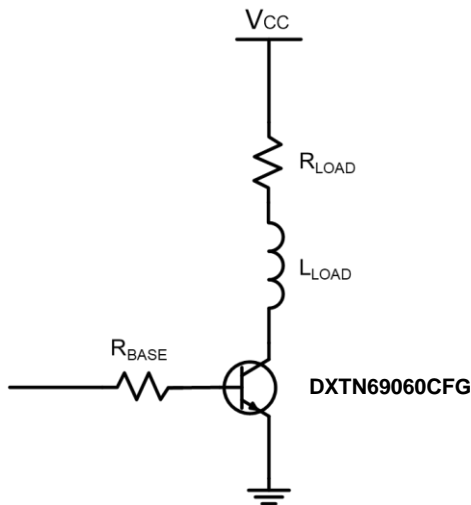


Fig. 13 DXTN69060CFG in a Low-Side Switch Configuration

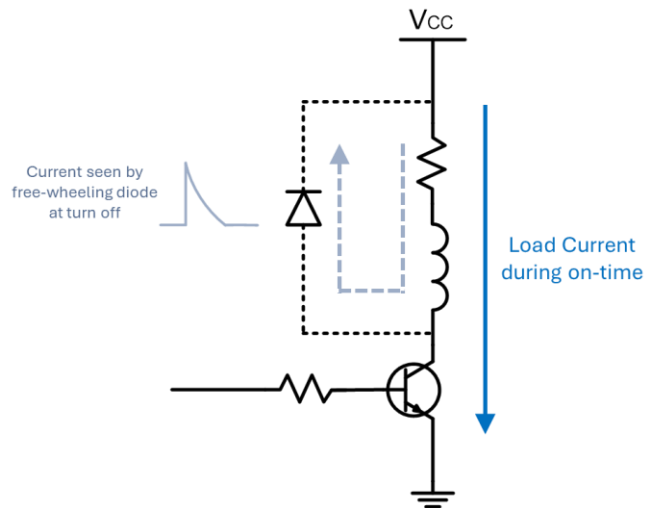


Fig. 14 Additional Free-Wheeling Diode Across Inductive Load for Voltage Spikes Suppression

The appropriate free-wheeling diode should have:

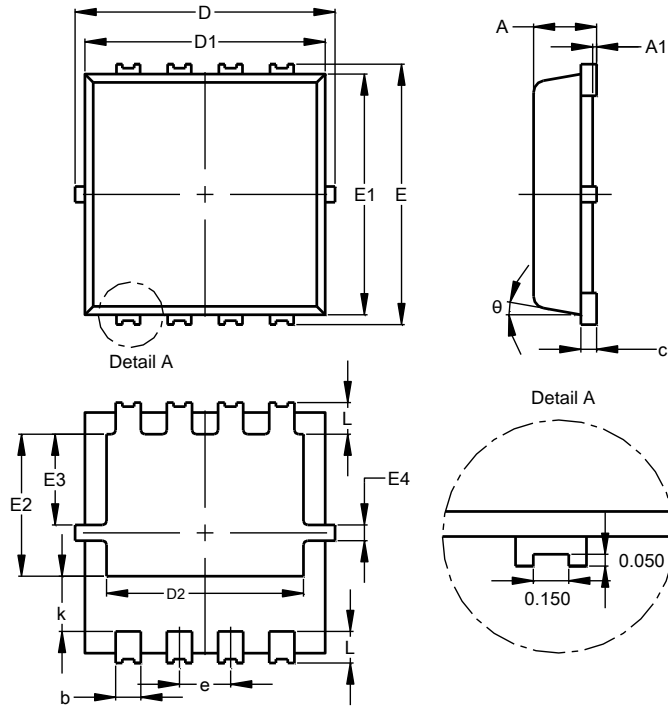
- An Average Rectified Output Current (I_O) rating of at least twice the full Load Current.
- A Working Peak Reverse Voltage (V_{RWM}) equal to the voltage applied to the load (minimum) or twice its value (recommended).

For example, in the figures above, $V_{CC} = 24V$ and $I_{LOAD} = 3A$. The PDS760 Schottky Barrier Rectifier with $I_O = 7A$ and $V_{RWM} = 60V$ will protect the transistor from turn-off inductive voltage spikes and ensure a safe system operation.

Package Outline Dimensions (Note 11)

Please see <https://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8/SWP (Type UX)



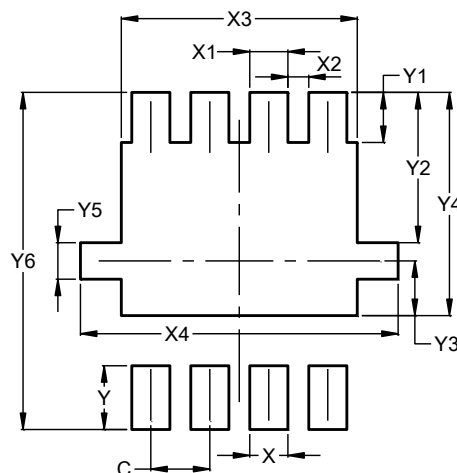
PowerDI3333-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Note: 11. Sidewall tin plated package for wettable flanks in AOI.

Suggested Pad Layout

Please see <https://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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